Panasonic

DRC3114T0L

Silicon NPN epitaxial planar type

For digital circuits
Complementary to DRA3114T
DRC9114T in SSSMini3 type package

■ Features

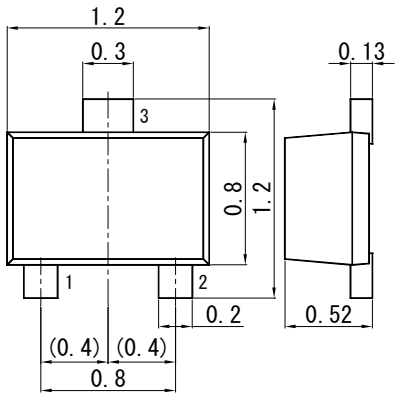
- High forward current transfer ratio hFE with excellent linearity
- Low collector-emitter saturation voltage Vce(sat)
- Halogen-free / RoHS compliant
  (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: ND

■ Packaging

Embossed type (Thermo-compression sealing) : 10 000 pcs / reel (standard)

Unit: mm



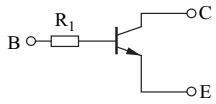
1. Base
2. Emitter
3. Collector

Panasonic	SSSMini3-F2-B
JEITA	SC-105AA
Code	SOT-723

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	VCBO	50	V
Collector-emitter voltage (Base open)	VCEO	50	V
Collector current	IC	100	mA
Total power dissipation	PT	100	mW
Junction temperature	Tj	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	°C

Internal Connection



Resistance value	R1	10	kΩ

■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	VCBO	IC = 10 μA, IE = 0	50			V
Collector-emitter voltage (Base open)	VCEO	IC = 2 mA, IB = 0	50			V
Collector-base cutoff current (Emitter open)	ICBO	VCB = 50 V, IE = 0			0.1	μA
Collector-emitter cutoff current (Base open)	ICEO	VCE = 50 V, IB = 0			0.5	μA
Emitter-base cutoff current (Collector open)	IEBO	VEB = 6 V, IC = 0			0.01	mA
Forward current transfer ratio	hFE	VCE = 10 V, IC = 5 mA	160		460	-
Collector-emitter saturation voltage	VCE(sat)	IC = 10 mA, IB = 0.5 mA			0.25	V
Input voltage	Vi(on)	VCE = 0.2 V, IC = 5 mA	1.2			V
	Vi(off)	VCE = 5 V, IC = 100 μA			0.4	V
Between emitter base resistance	R1		-30%	10	+30%	kΩ

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.